

Fig

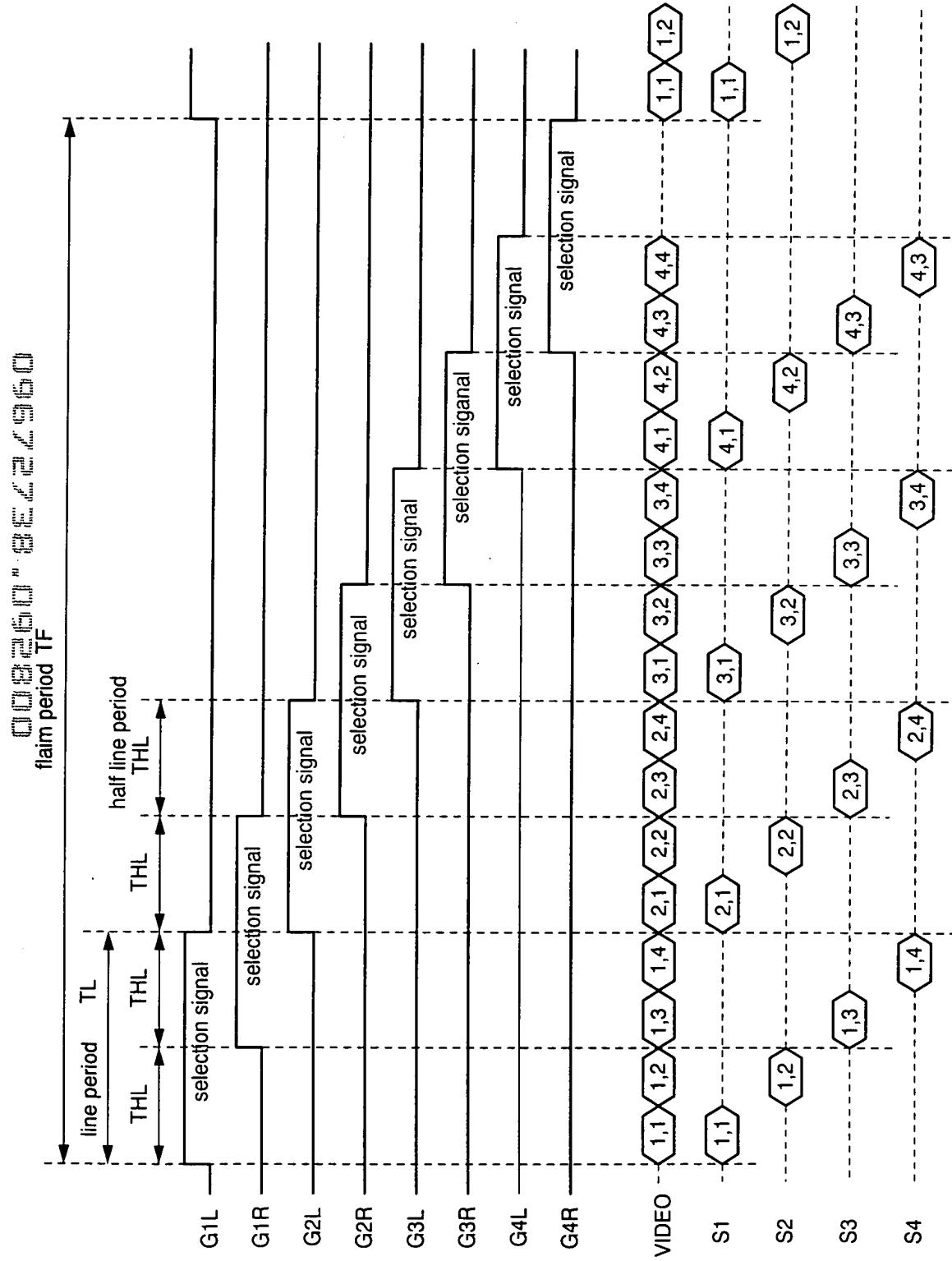


Fig.2

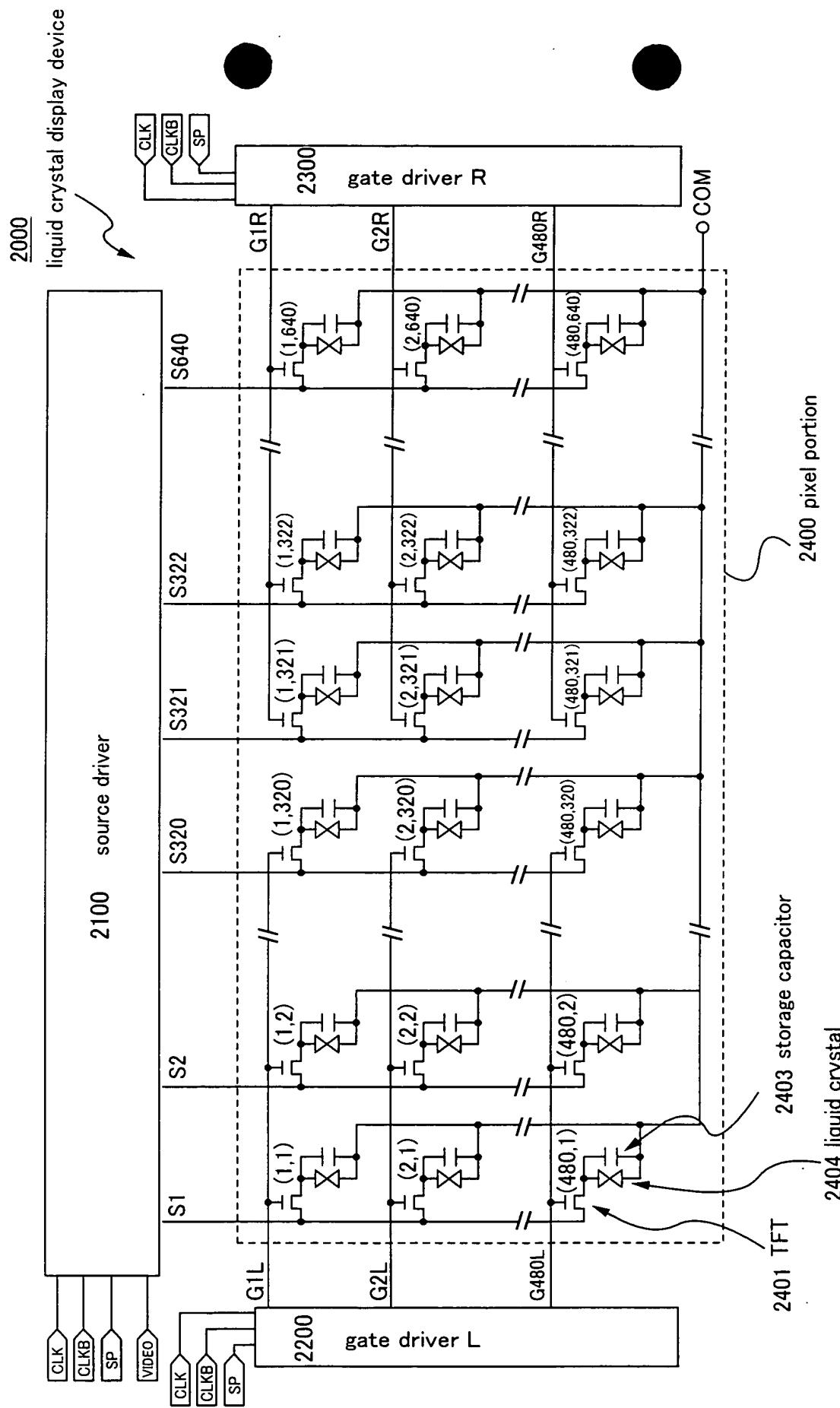


Fig.3

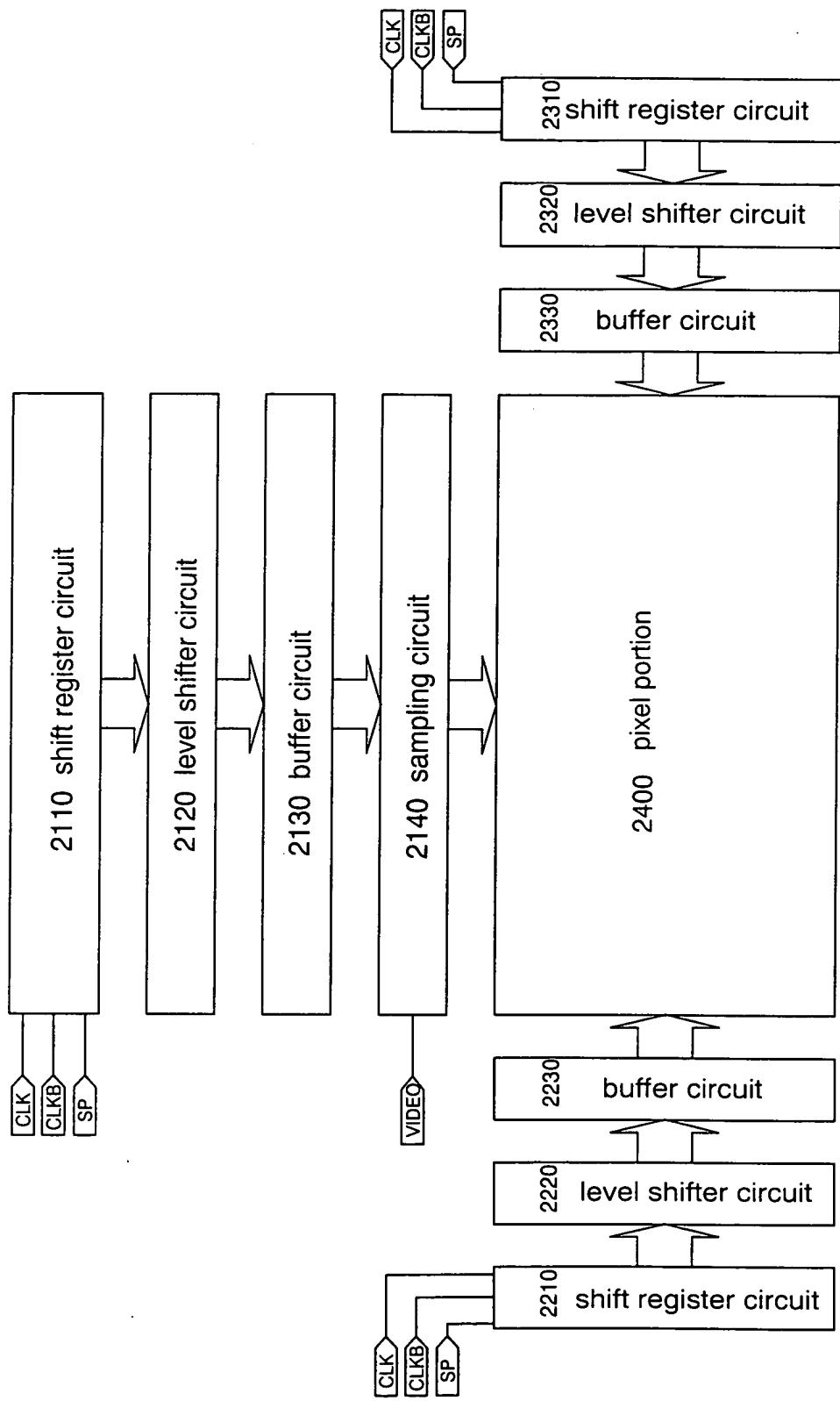


Fig.4

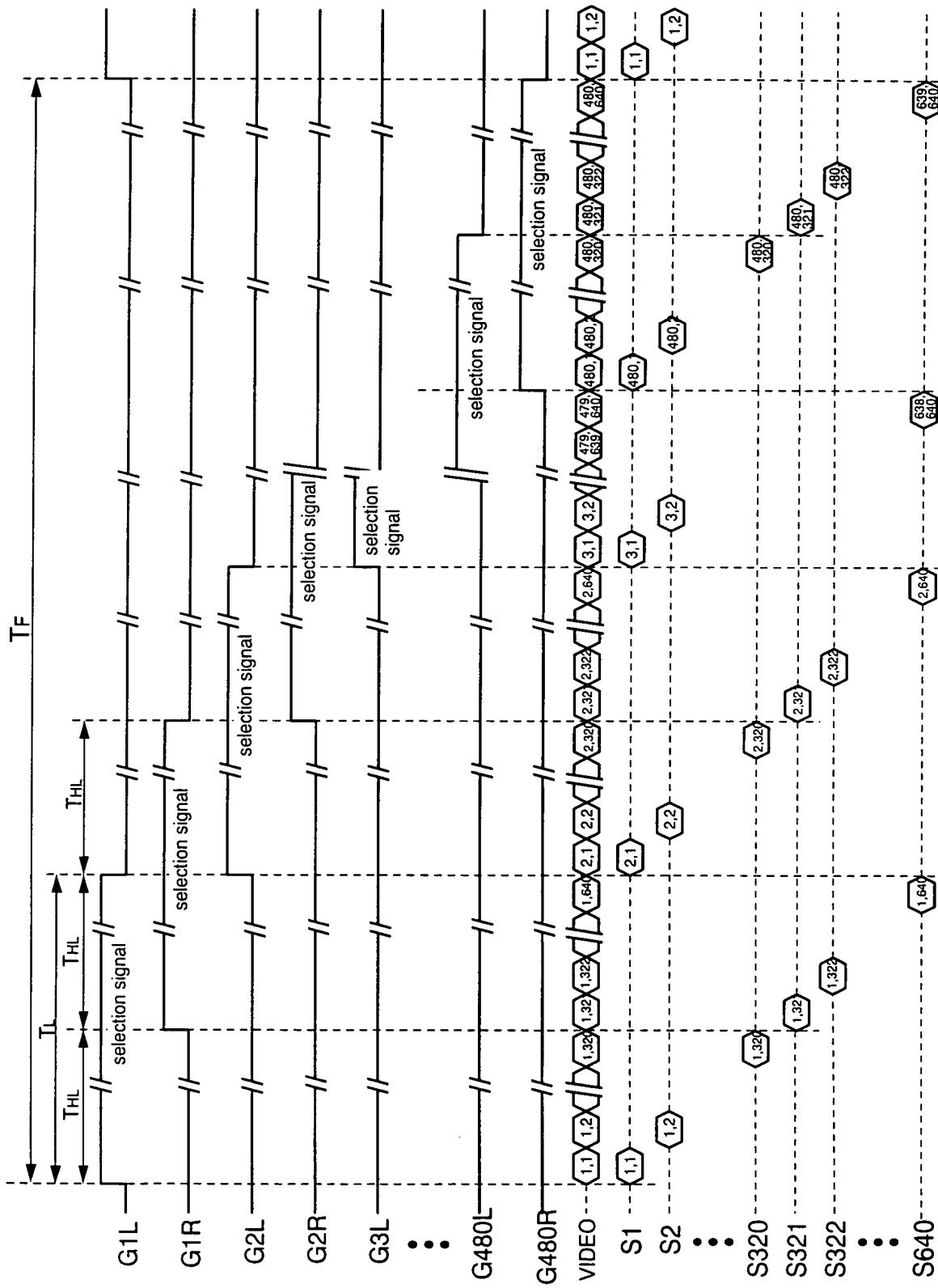


Fig. 5

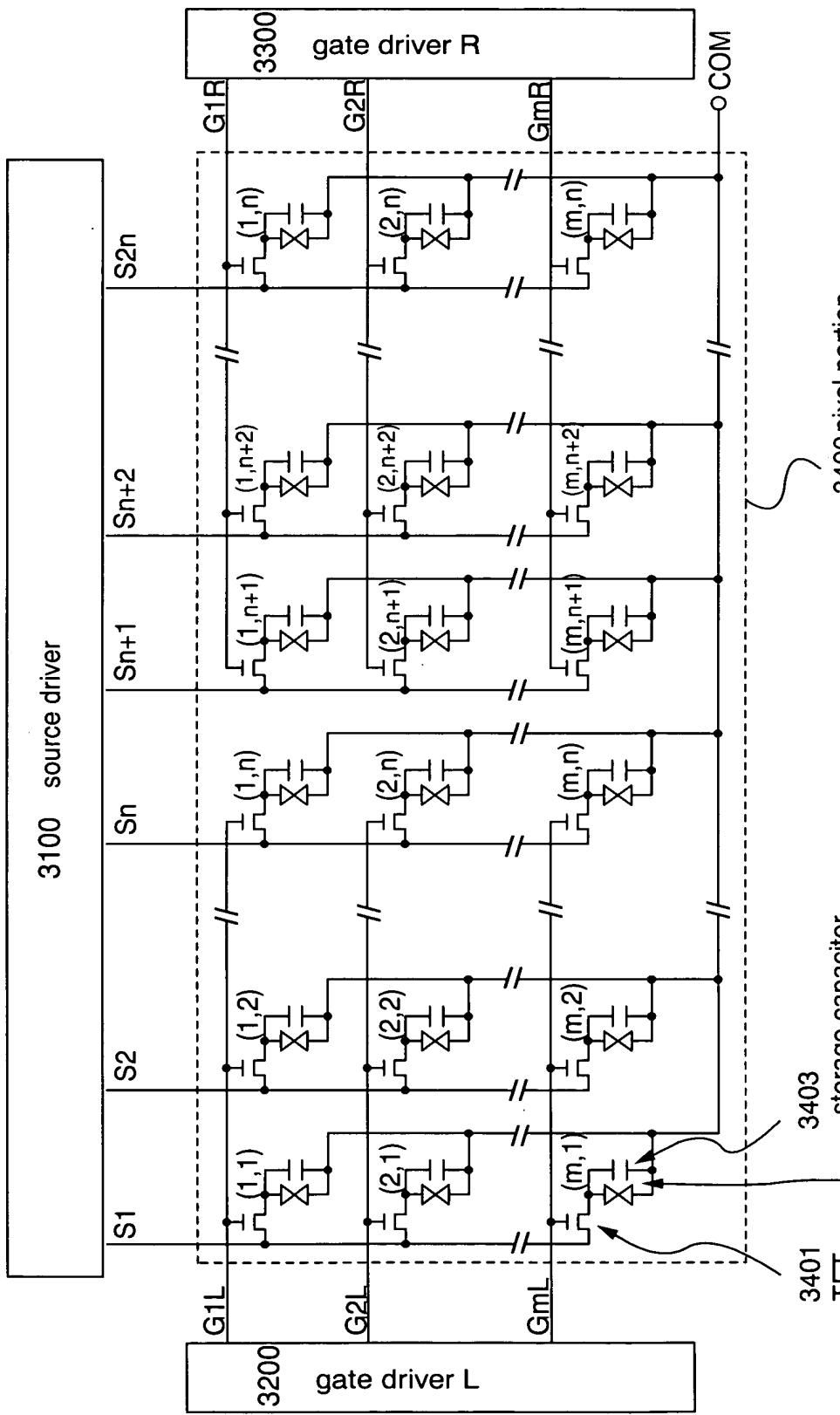


Fig.6

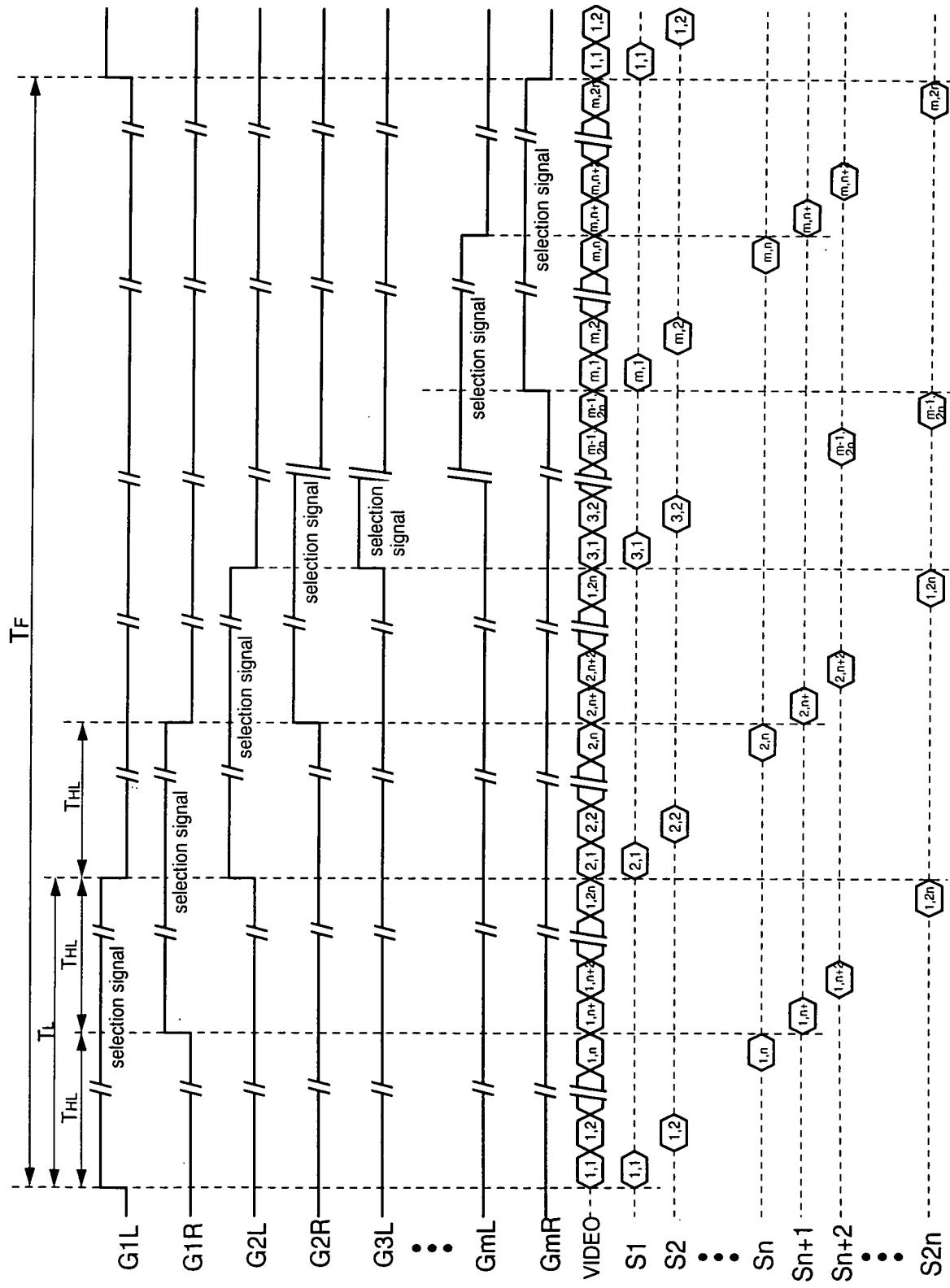


Fig. 7

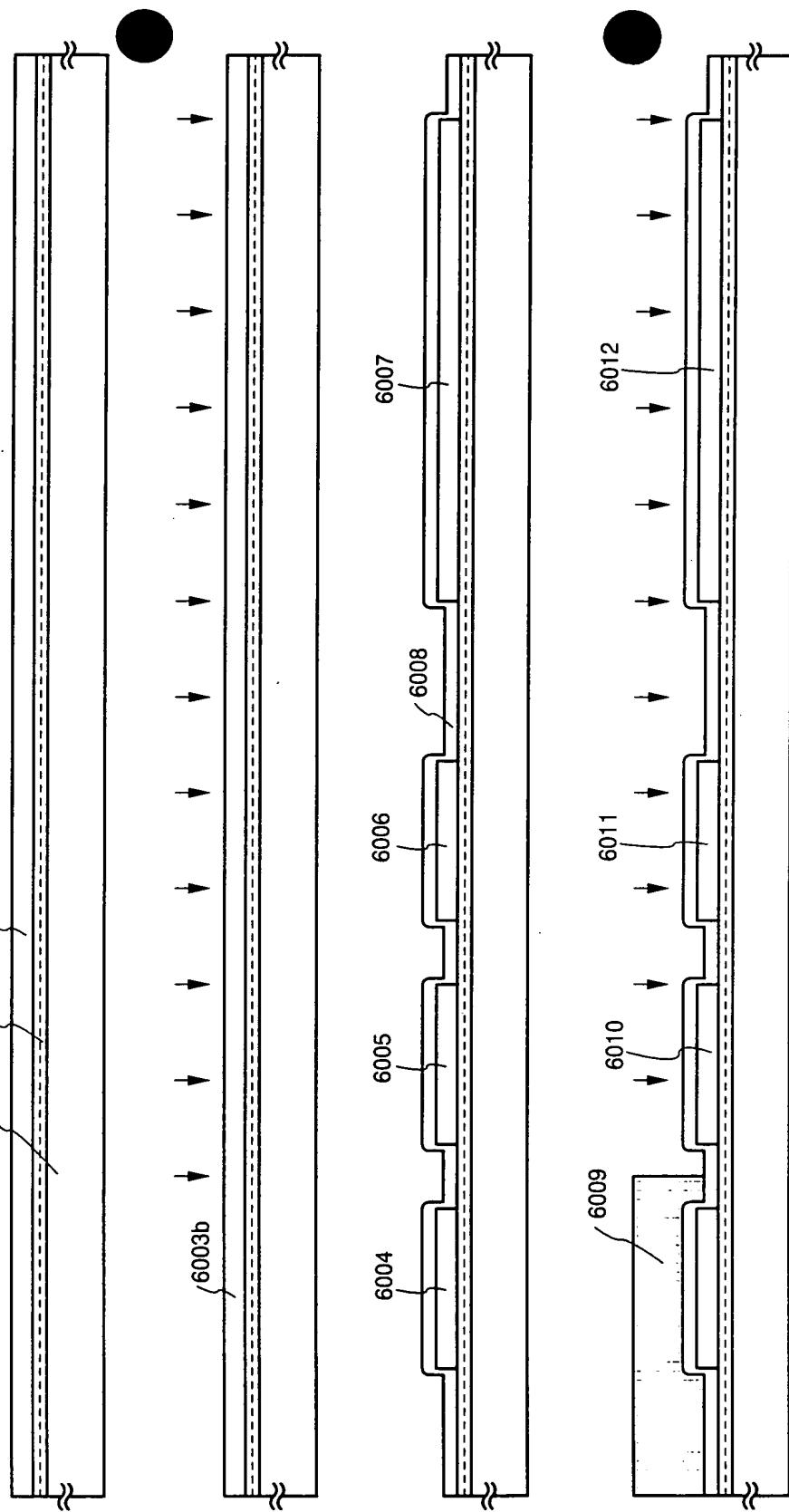


Fig. 8A

Fig. 8B

Fig. 8C

Fig. 8D

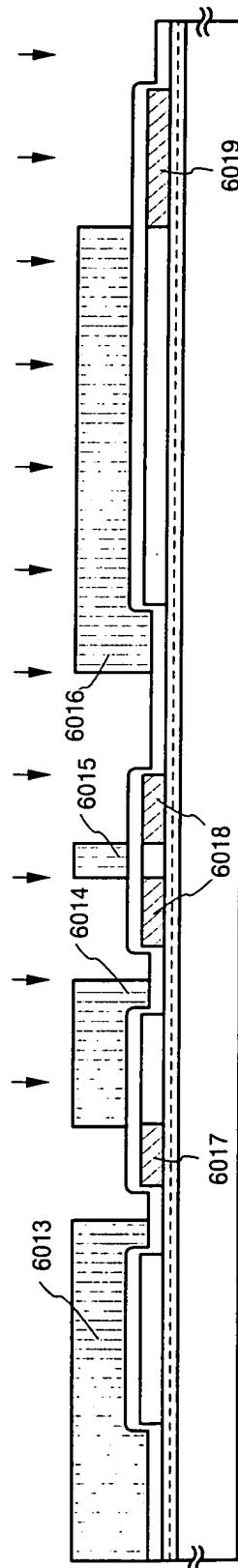


Fig. 9A

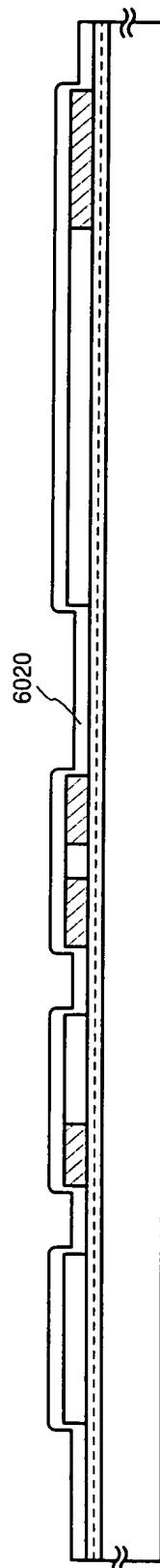


Fig. 9B

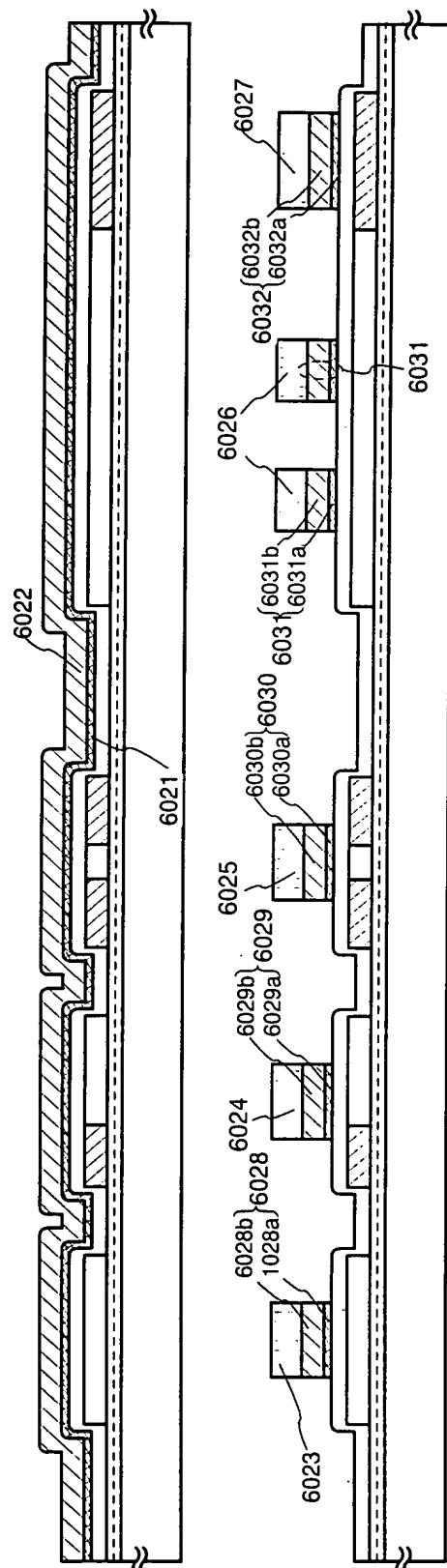


Fig. 9C

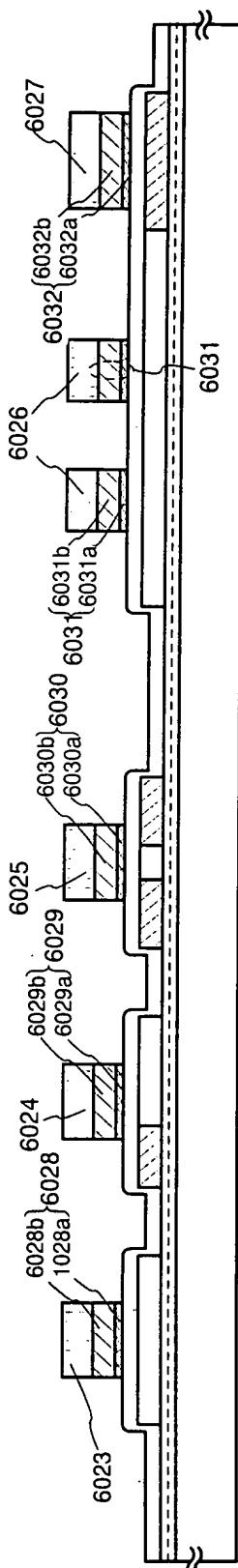


Fig. 9D

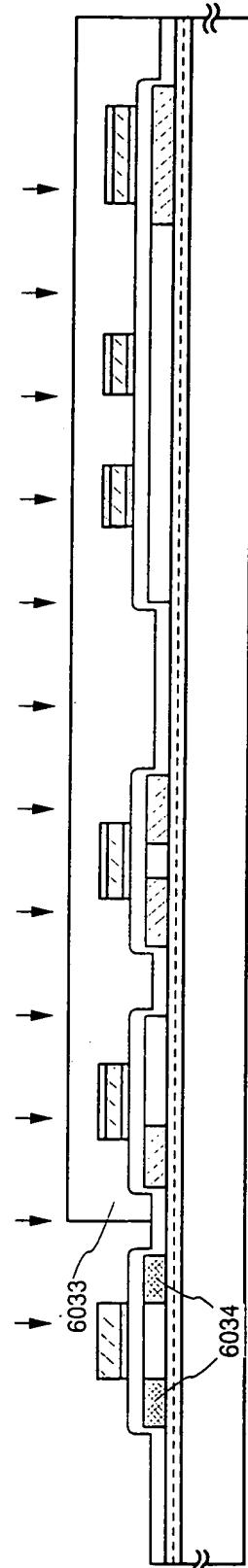


Fig. 10A

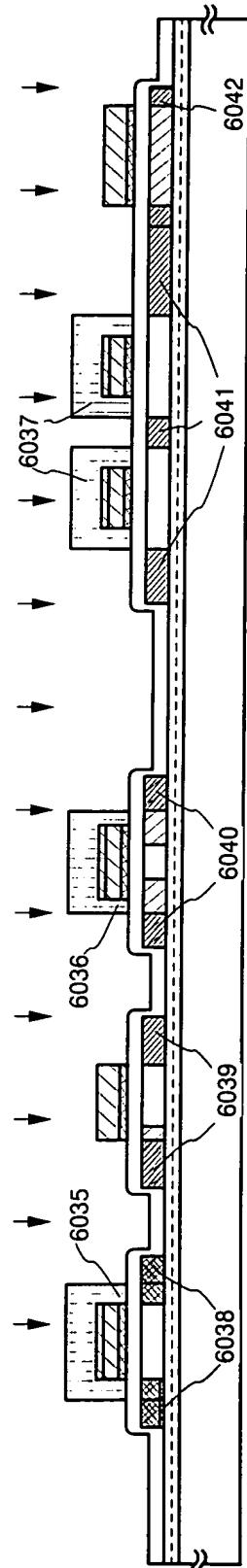


Fig. 10B

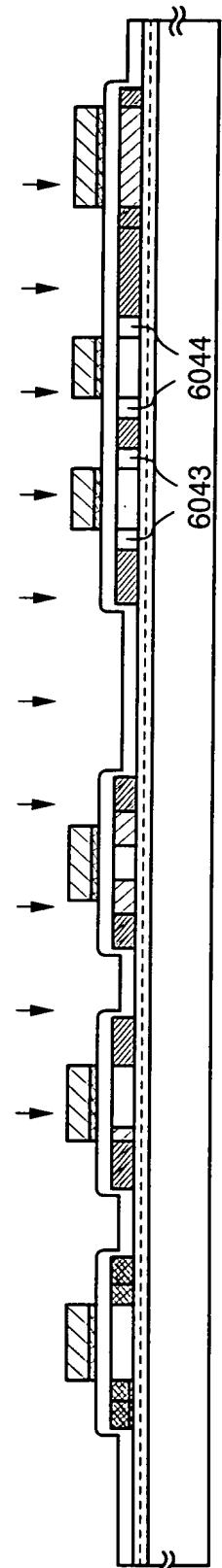


Fig. 10C

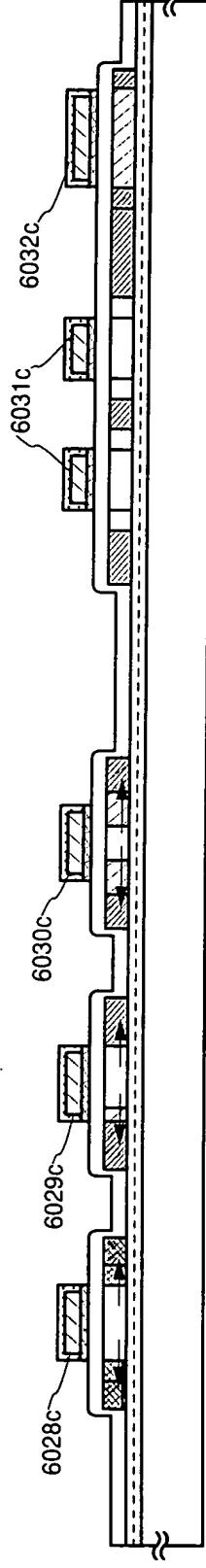


Fig. 10D

009260 " 35 24 960

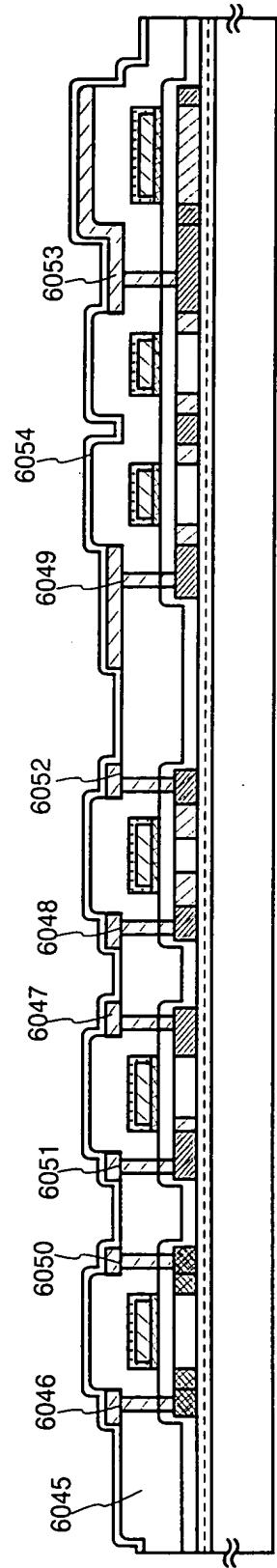


Fig. 11A

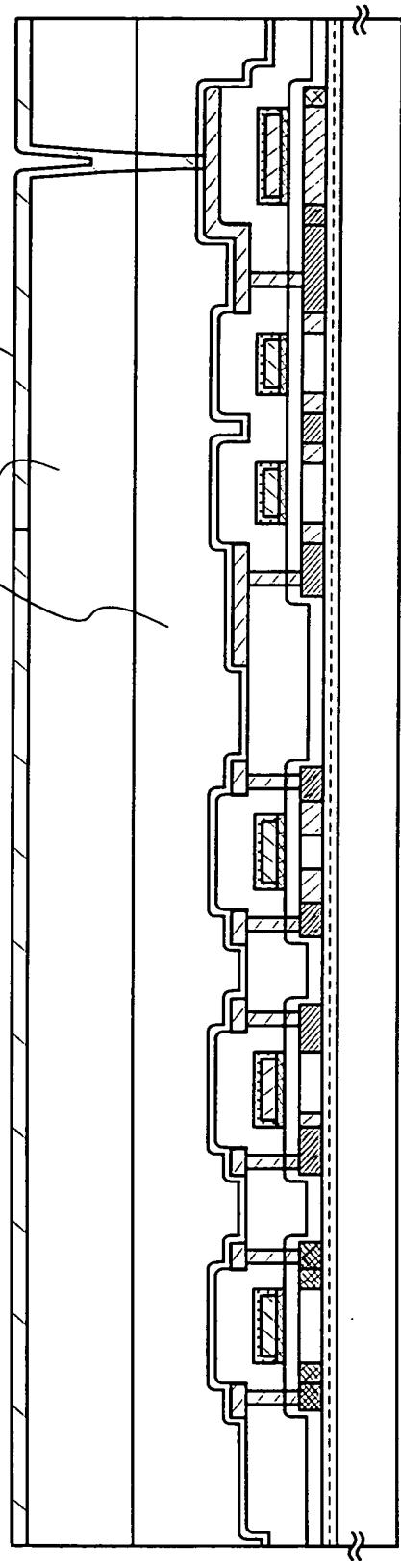
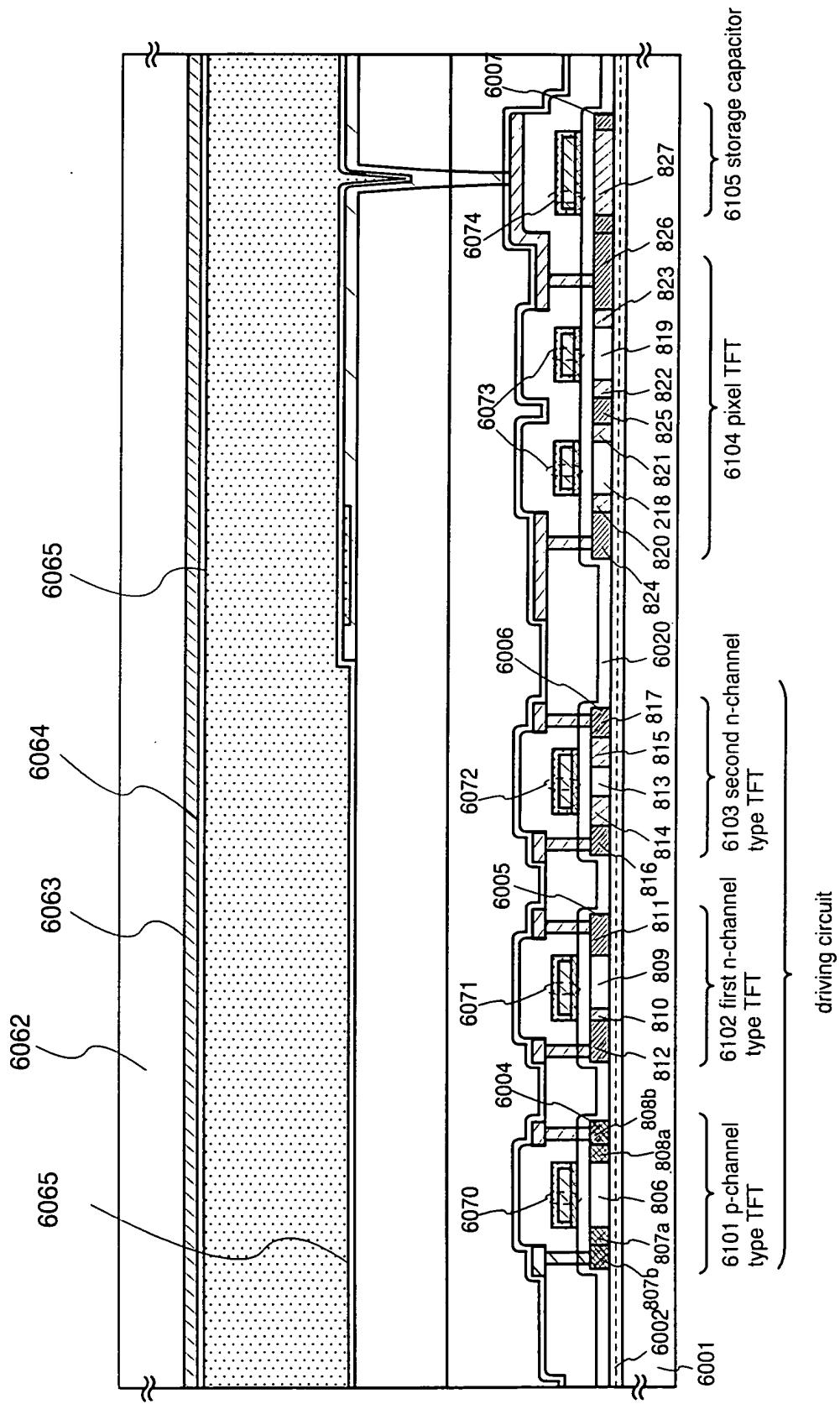


Fig. 11B



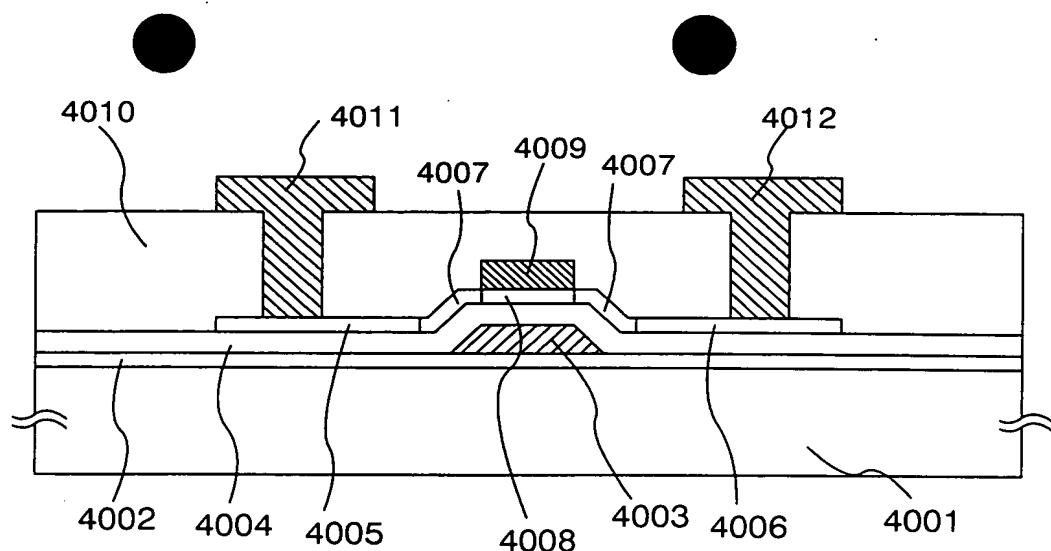
driving circuit

driving circuit

driving circuit

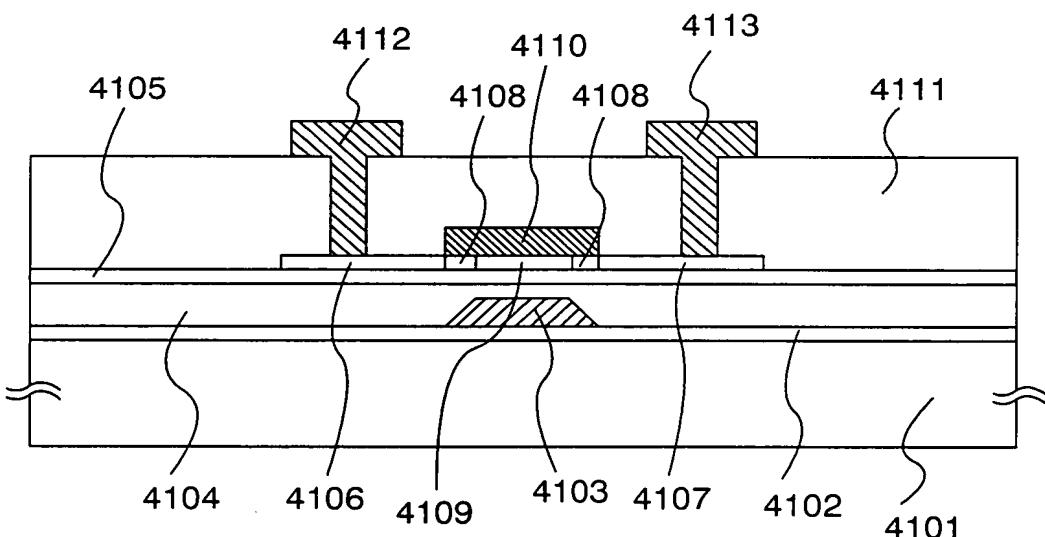
driving circuit

Fig.13A



4001 substrate	4007 low concentration impurity region(LDD region)
4002 silicon oxide film	4008 channel forming region
4003 gate electrode	4009 channel protective film
4004 gate insulating film	4010 interlayer insulating film
4005 source region	4011 source electrode
4006 drain region	4012 drain electrode

Fig.13B



4101 substrate	4108 low concentration impurity region(LDD region)
4102 silicon oxide film	4109 channel forming region
4103 gate electrode	4110 channel protecting film
4104 bezocyclobutene(BCB)	4111 interlayer insulating film
4105 silicon nitride film	4112 source electrode
4106 source region	4113 drain electrode
4107 drain region	

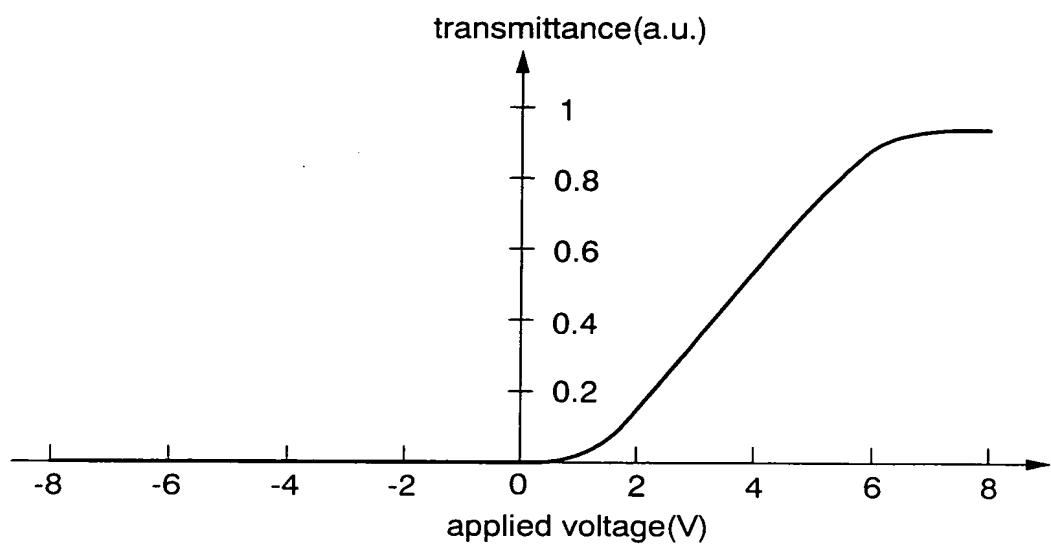


Fig.14

Fig.15A

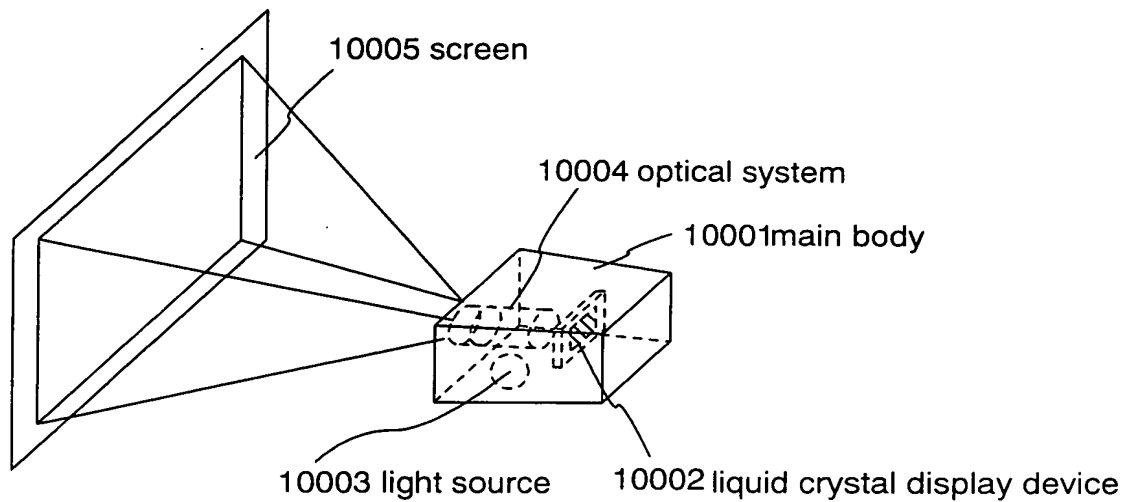
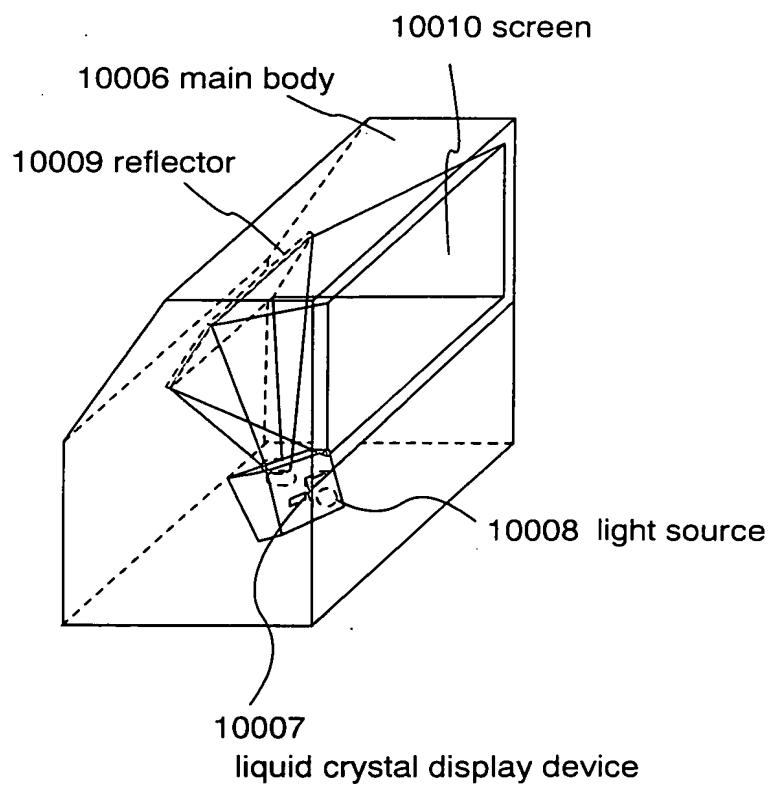


Fig.15B



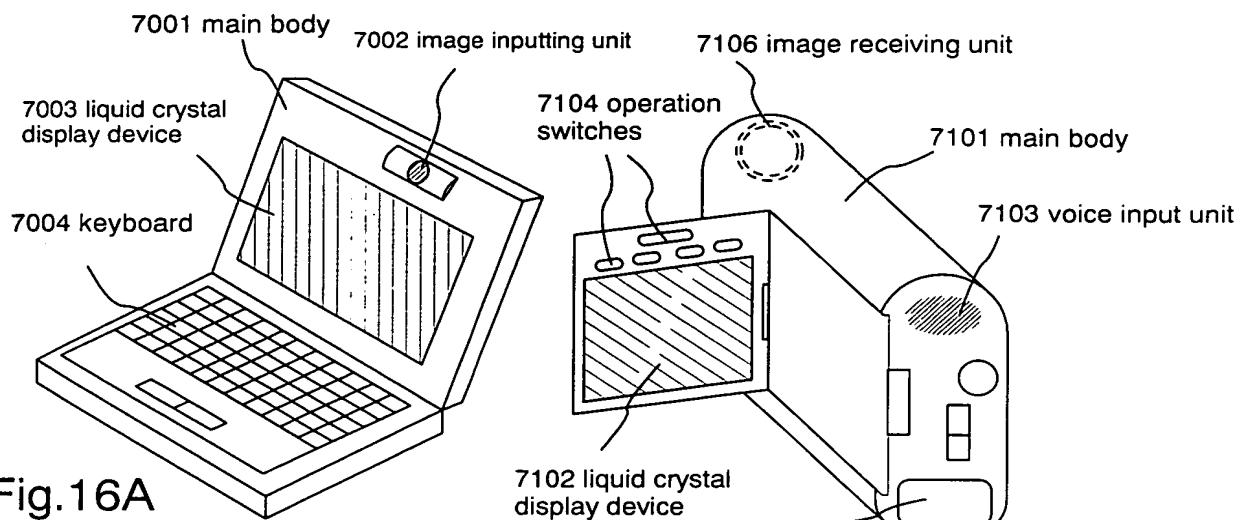


Fig.16A

Fig.16B

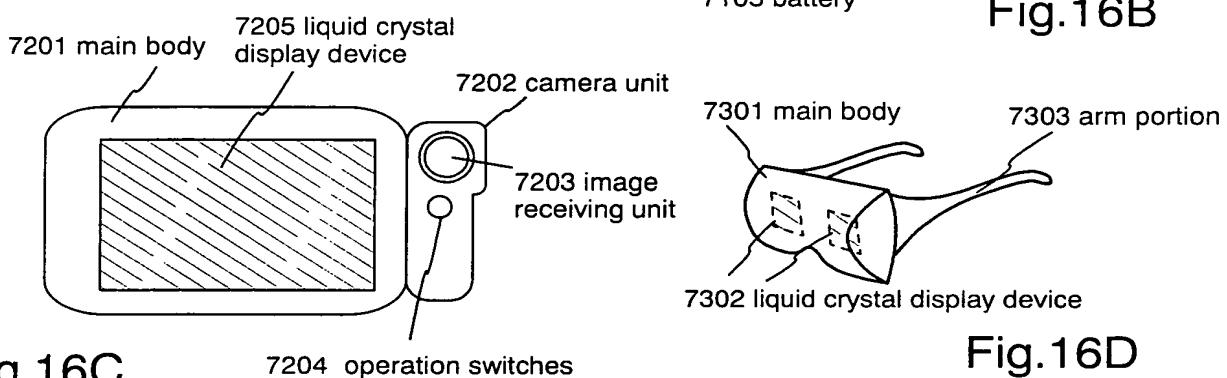


Fig.16C

Fig.16D

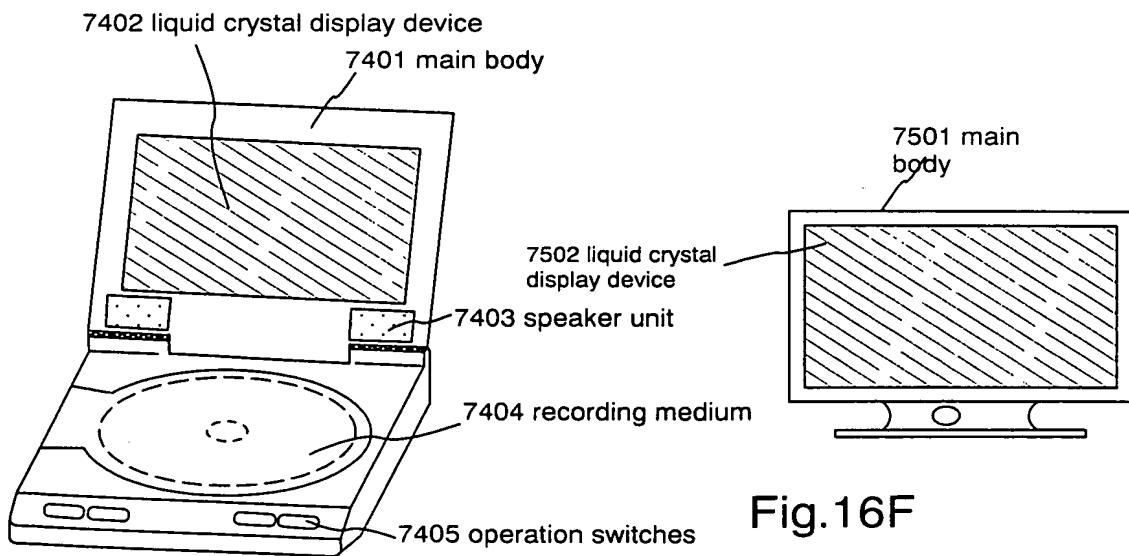


Fig.16E

Fig.16F

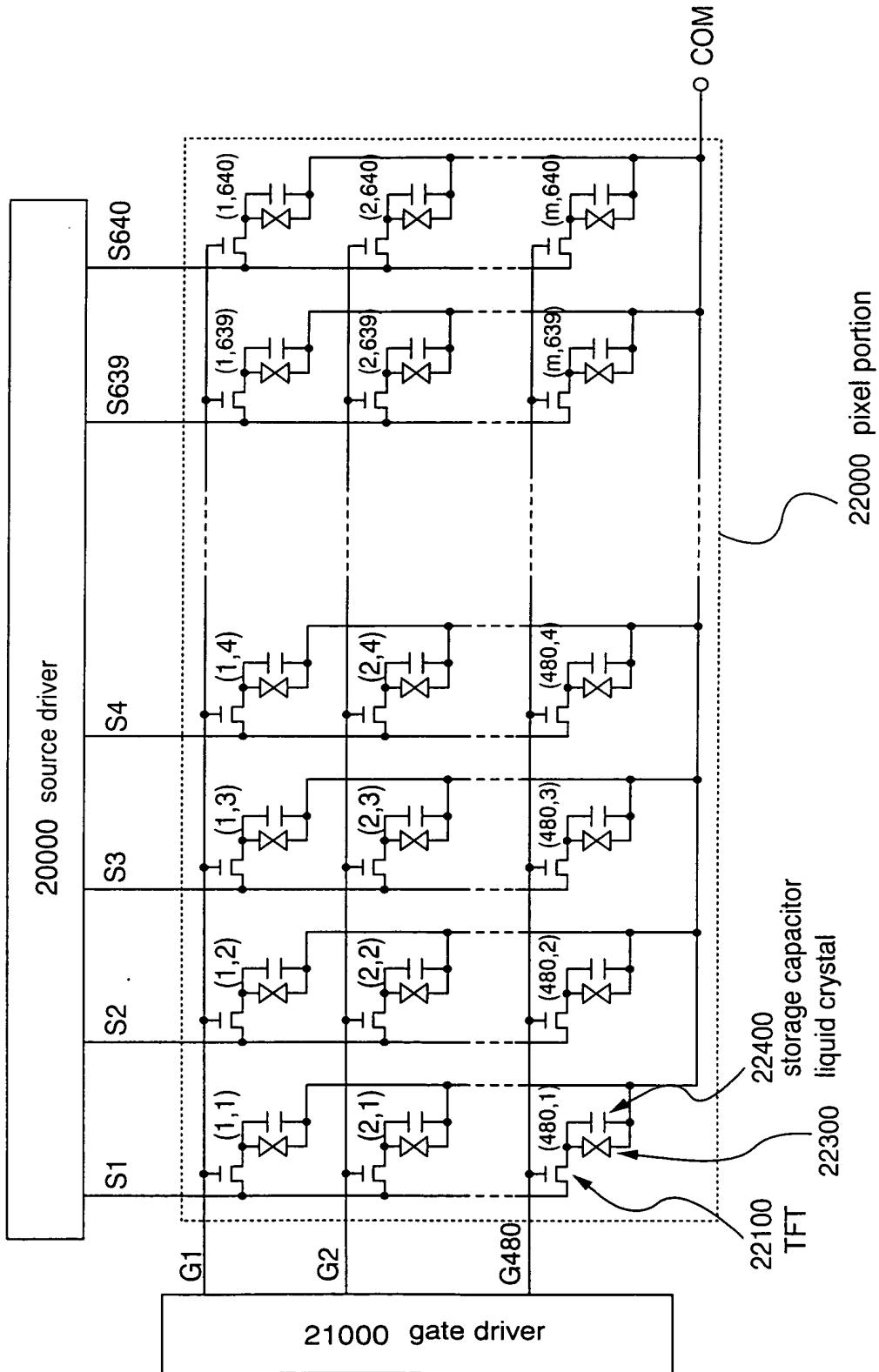


Fig. 17

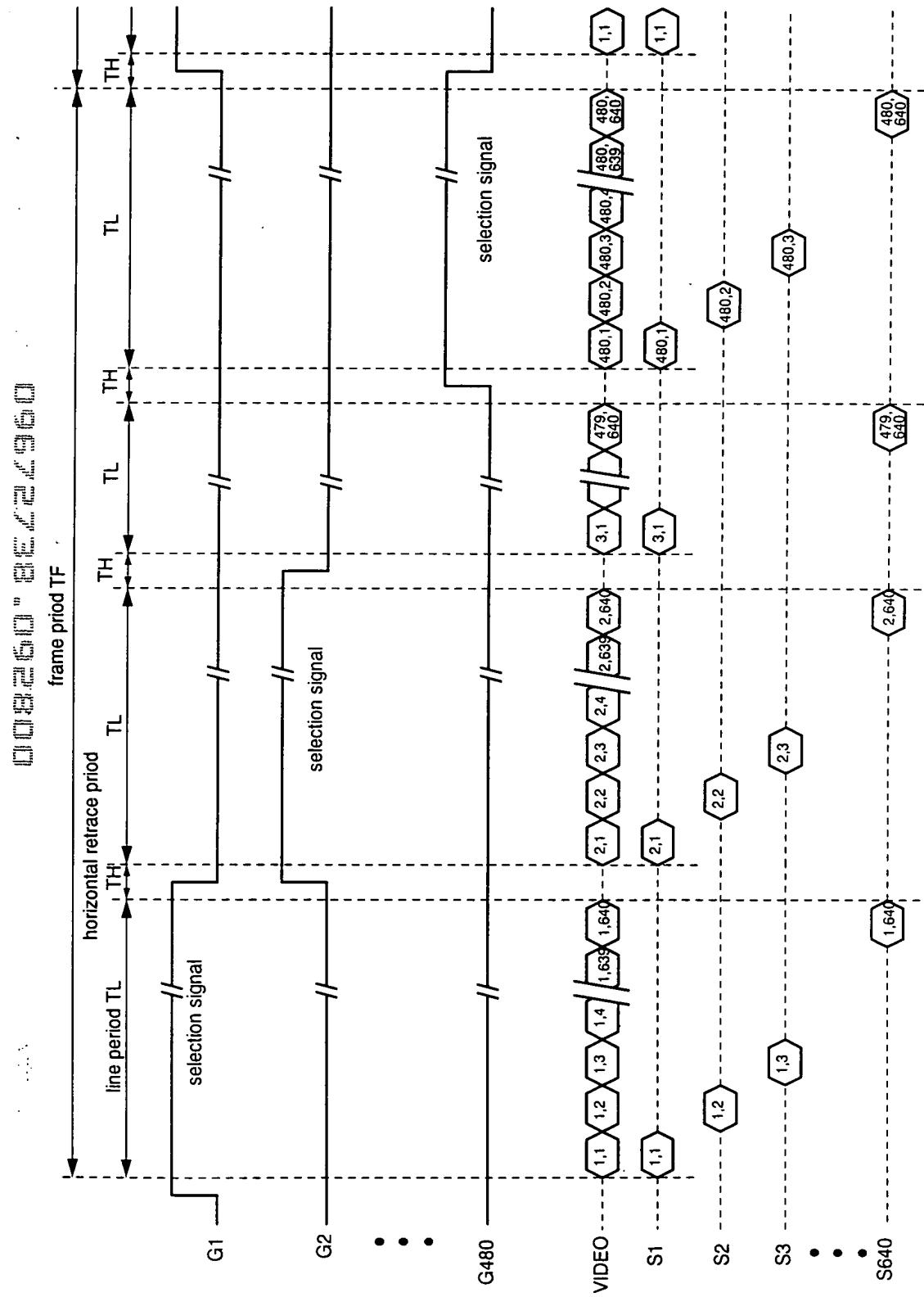


Fig. 18

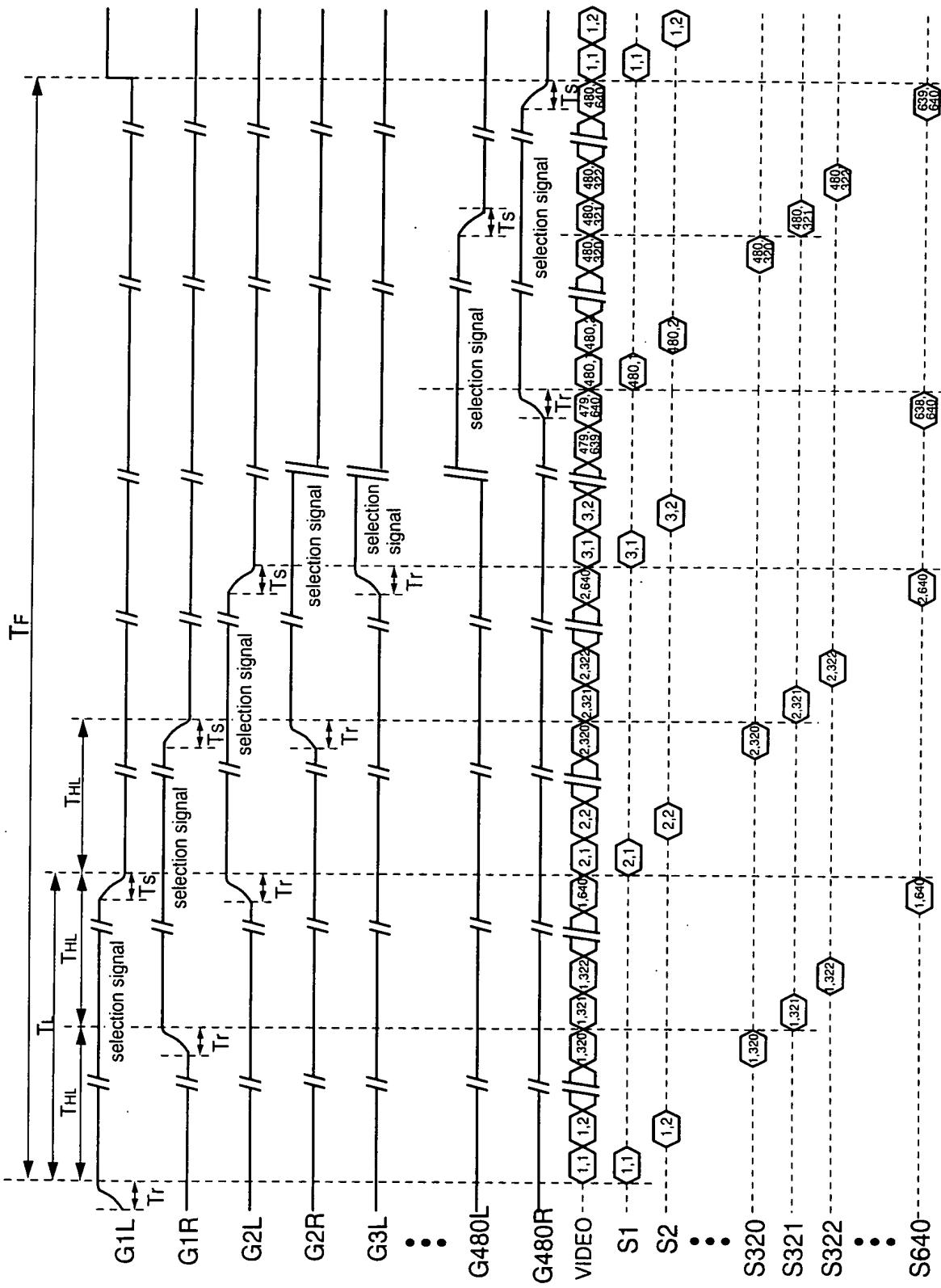


Fig. 19